

**General Description**

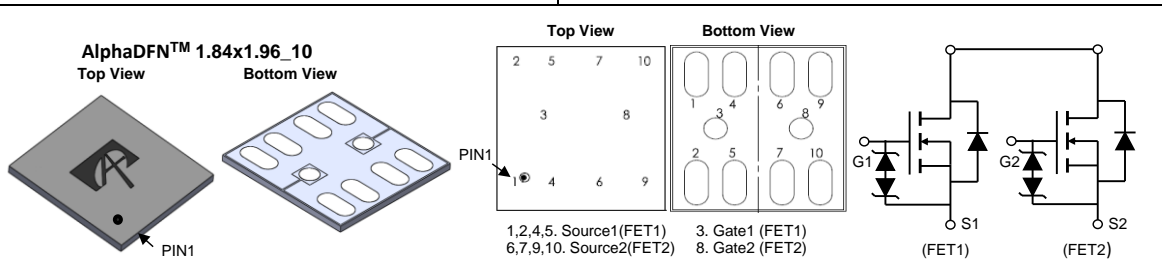
- Trench Power MOSFET Technology
- Low  $R_{SS(ON)}$
- With ESD protection to improve battery performance and safety
- Common drain configuration for design simplicity
- RoHS and Halogen-Free Compliant

**Applications**

- Battery protection switch
- Mobile device battery charging and discharging

**Product Summary**

$V_{SS}$	12V
$R_{SS(ON)}$ (at $V_{GS}=4.5V$ )	< 3.4m $\Omega$
$R_{SS(ON)}$ (at $V_{GS}=3.8V$ )	< 3.8m $\Omega$
$R_{SS(ON)}$ (at $V_{GS}=3.1V$ )	< 4.4m $\Omega$
$R_{SS(ON)}$ (at $V_{GS}=2.5V$ )	< 5.3m $\Omega$

**Typical ESD protection**
**HBM Class 2**


Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOCA32106E	AlphaDFN™ 1.84x1.96_10	Tape & Reel	8000

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Rating	Units
Source-Source Voltage	$V_{SS}$	12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Source Current(DC) <sup>Note1</sup>	$I_S$	25	A
Source Current(Pulse) <sup>Note2</sup>	$I_{SM}$	130	A
Power Dissipation <sup>Note1</sup>	$P_D$	2.8	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typical	Units
Maximum Junction-to-Ambient $t \leq 10s$	$R_{\theta JA}$	35	$^\circ\text{C/W}$
Maximum Junction-to-Ambient Steady-State		45	$^\circ\text{C/W}$

**Note 1.**  $I_S$  rated value is based on bare silicon. Mounted on 70mmx70mm FR-4 board.

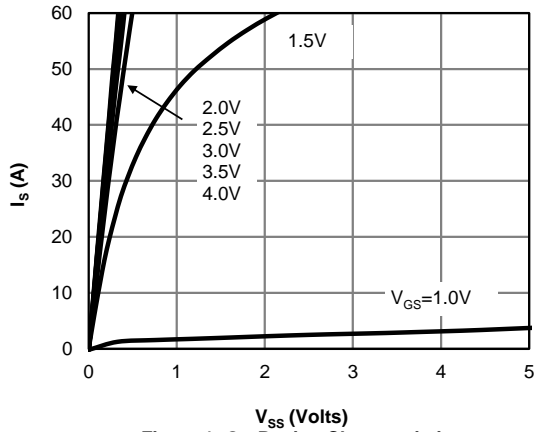
**Note 2.** PW < 10  $\mu s$  pulses, duty cycle 1% max.

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

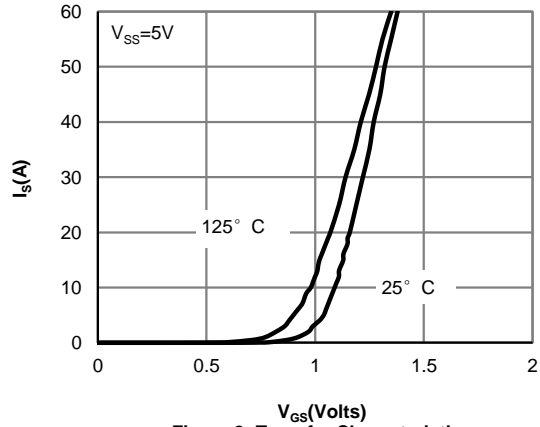
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>SSS</sub>	Source-Source Breakdown Voltage	I <sub>S</sub> =250μA, V <sub>GS</sub> =0V Test Circuit 6	12			V
I <sub>SSS</sub>	Zero Gate Voltage Source Current	V <sub>SS</sub> =12V, V <sub>GS</sub> =0V Test Circuit 1 T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate leakage current	V <sub>SS</sub> =0V, V <sub>GS</sub> =±8V Test Circuit 2			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>SS</sub> =V <sub>GS</sub> , I <sub>S</sub> =250μA Test Circuit 3	0.4	0.7	1.1	V
R <sub>SS(ON)</sub>	Static Source to Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>S</sub> =5A Test Circuit 4 T <sub>J</sub> =125°C	1.9	2.8	3.4	mΩ
		V <sub>GS</sub> =3.8V, I <sub>S</sub> =5A Test Circuit 4	2.1	3.1	3.8	
		V <sub>GS</sub> =3.1V, I <sub>S</sub> =5A Test Circuit 4	2.3	3.4	4.4	
		V <sub>GS</sub> =2.5V, I <sub>S</sub> =5A Test Circuit 4	2.7	3.9	5.3	
g <sub>FS</sub>	Forward Transconductance	V <sub>SS</sub> =5V, I <sub>S</sub> =5A Test Circuit 3		50		S
V <sub>FSS</sub>	Forward Source to Source Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V Test Circuit 5		0.55	1	V
<b>DYNAMIC PARAMETERS</b>						
R <sub>g</sub>	Gate resistance	f=1MHz		1.5		KΩ
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS1</sub> =4.5V, V <sub>SS</sub> =6V, I <sub>S</sub> =5A		23		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS1</sub> =4.5V, V <sub>SS</sub> =6V, R <sub>L</sub> =1.2Ω, R <sub>GEN</sub> =3Ω Test Circuit8		1.1		μs
t <sub>r</sub>	Turn-On Rise Time			3.2		μs
t <sub>D(off)</sub>	Turn-Off DelayTime			5.3		μs
t <sub>f</sub>	Turn-Off Fall Time			11		μs

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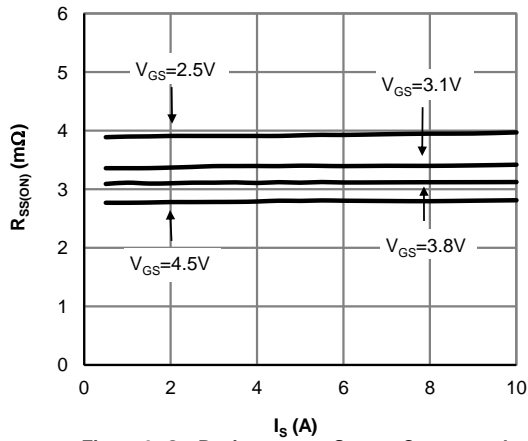
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



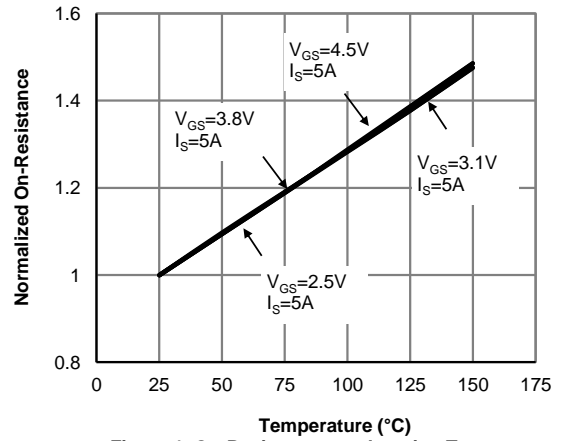
**Figure 1: On-Region Characteristics**



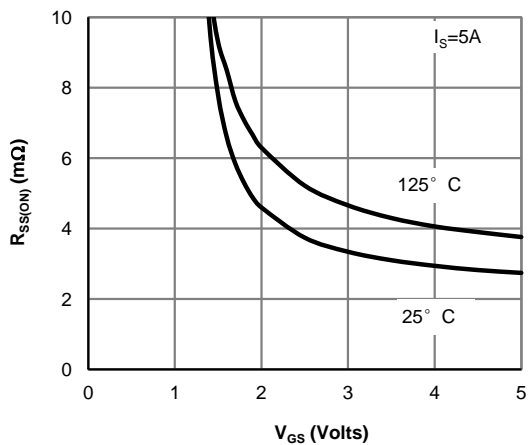
**Figure 2: Transfer Characteristics**



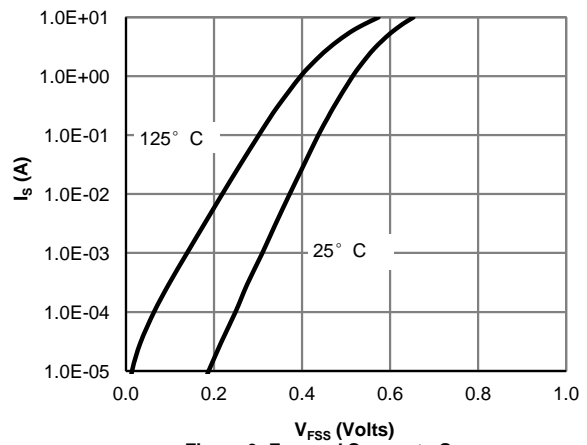
**Figure 3: On-Resistance vs. Source Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**

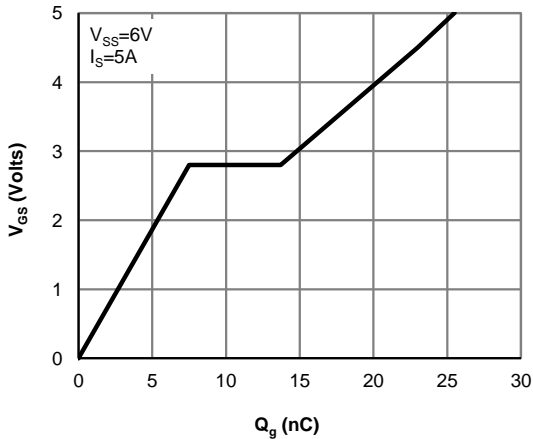


**Figure 5: On-Resistance vs. Gate-Source Voltage**

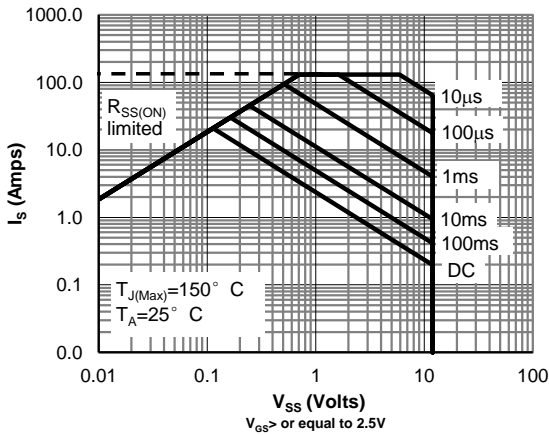


**Figure 6: Forward Source to Source Characteristics**

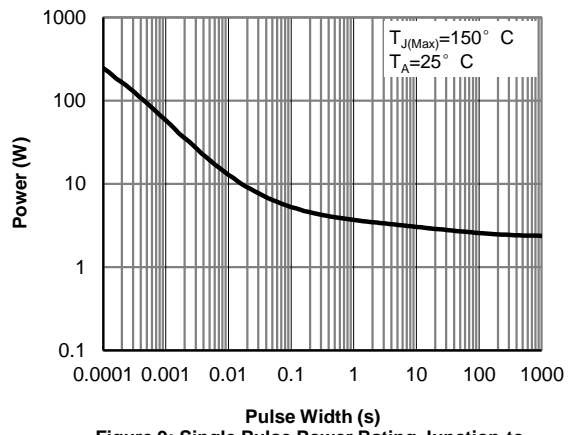
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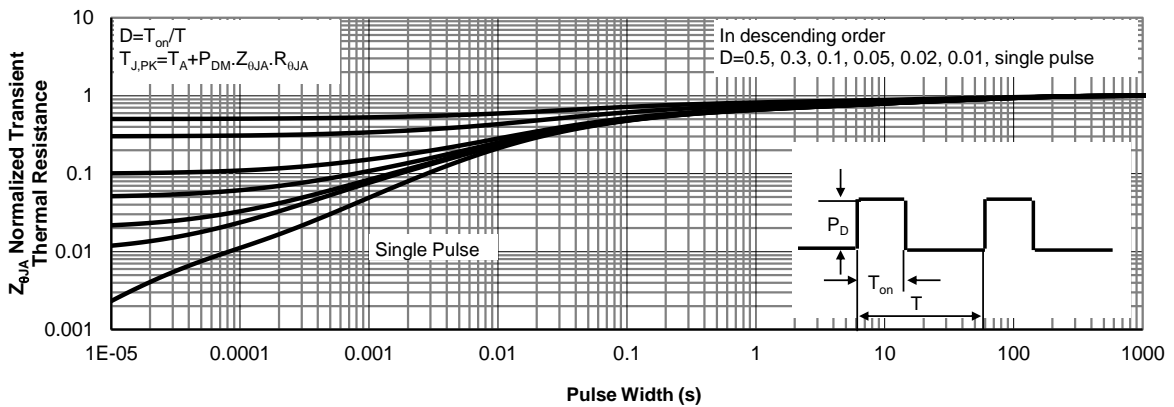
**Figure 7: Gate-Charge Characteristics**



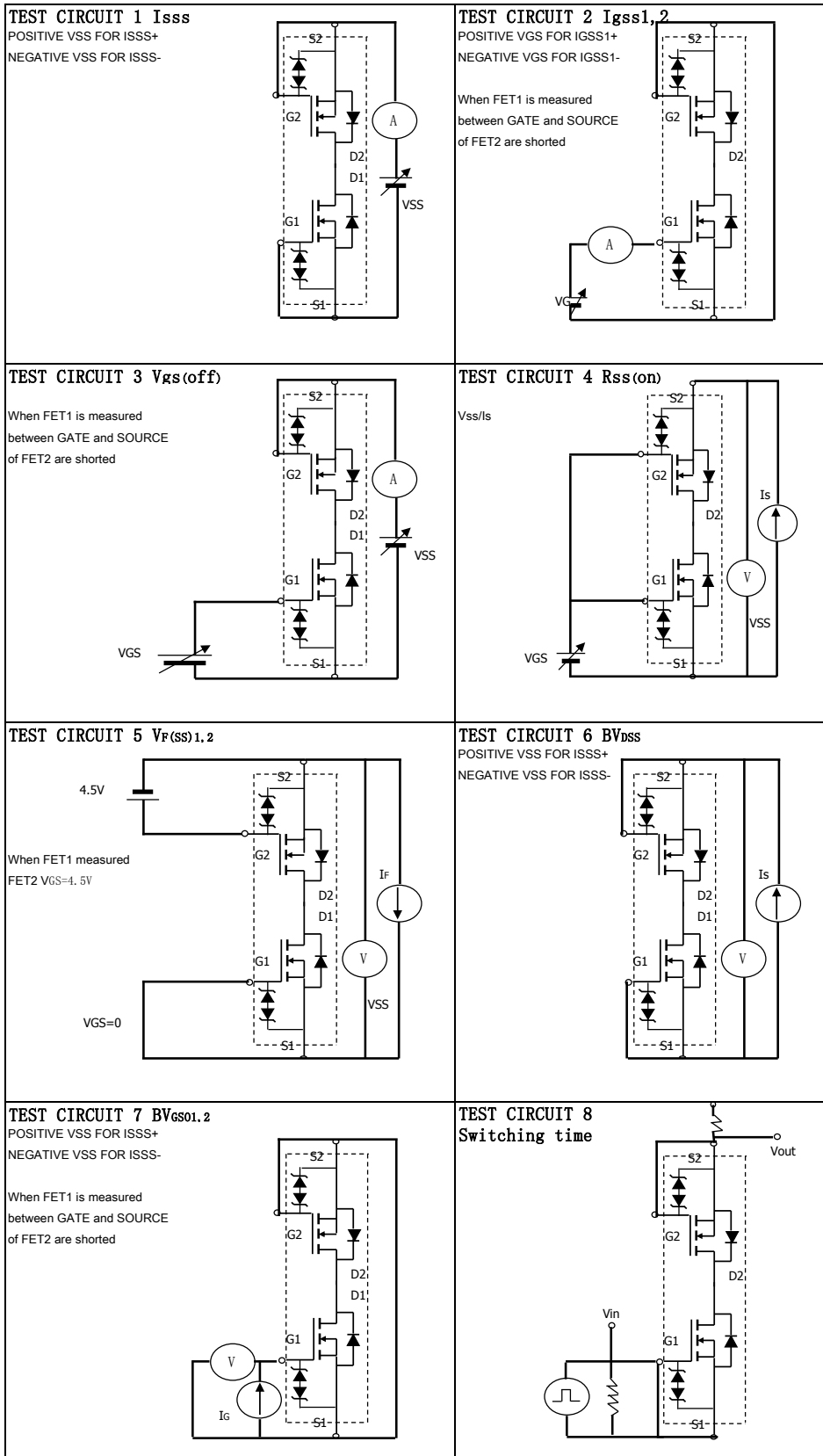
**Figure 8: Maximum Forward Biased Safe Operating Area (Note1)**



**Figure 9: Single Pulse Power Rating Junction-to-Ambient (Note1)**



**Figure 10: Normalized Maximum Transient Thermal Impedance (Note1)**



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